[Claims]

[Claim 1]

A cleaning solution composition for cleaning a semiconductor substrate or glass substrate surface, comprising one or more inorganic acids that contain fluorine atoms within their structure or salts thereof, water, one or more reducing agent, and one or more anionic surfactants, wherein anionic surfactant is a condensate of naphthalenesulfonic acid and formaldehyde or a salt thereof, and having hydrogen ion concentration (pH) of less than 7.

[Claim 2]

The cleaning solution composition according to Claim 1, wherein the inorganic acid that contains fluorine atoms within its structure is hydrofluoric acid, hexafluorosilicic acid or hexafluoroboric acid or combinations thereof.

[Claim 3]

The cleaning solution composition according to Claim 1, wherein the salt of the inorganic acid that contains fluorine atoms is an ammonium salt, amine salt or quaternary ammonium salt or combination thereof.

[Claim 4]

The cleaning solution composition according to any one of Claims 1 to 3, wherein the reducing agent is selected from a group consisting of five- or six-membered cyclic compounds having two or more hydroxyl groups.

[Claim 5]

The cleaning solution composition according to Claim 4, wherein five- or six-membered cyclic compound having two or more hydroxyl groups is ascorbic acid, catechol, resorcinol, hydroquinone, pyrogallol or methylcatechol.

[Claim 6]

The cleaning solution composition according to any one of Claims 1 to 5 for cleaning residual cerium compound on a semiconductor substrate or glass substrate surface after performing chemical machine polishing (CMP) of the semiconductor substrate or glass substrate surface using slurry containing a cerium compound as abrasive grain.

[Claim 7]

A stock solution composition for the cleaning solution composition according to any one of Claims 1 to 6 for use in producing the cleaning solution composition by being diluted by from 10-fold to 1000-fold.

[Claim 8]

A method of manufacturing a electronic device comprising steps of performing chemical machine polishing (CMP) of a semiconductor substrate or glass substrate surface using slurry containing a cerium compound as abrasive grain, and then cleaning residual cerium compound on the

semiconductor substrate or glass substrate surface using the cleaning solution composition according to any one of Claims 1 to 6.